



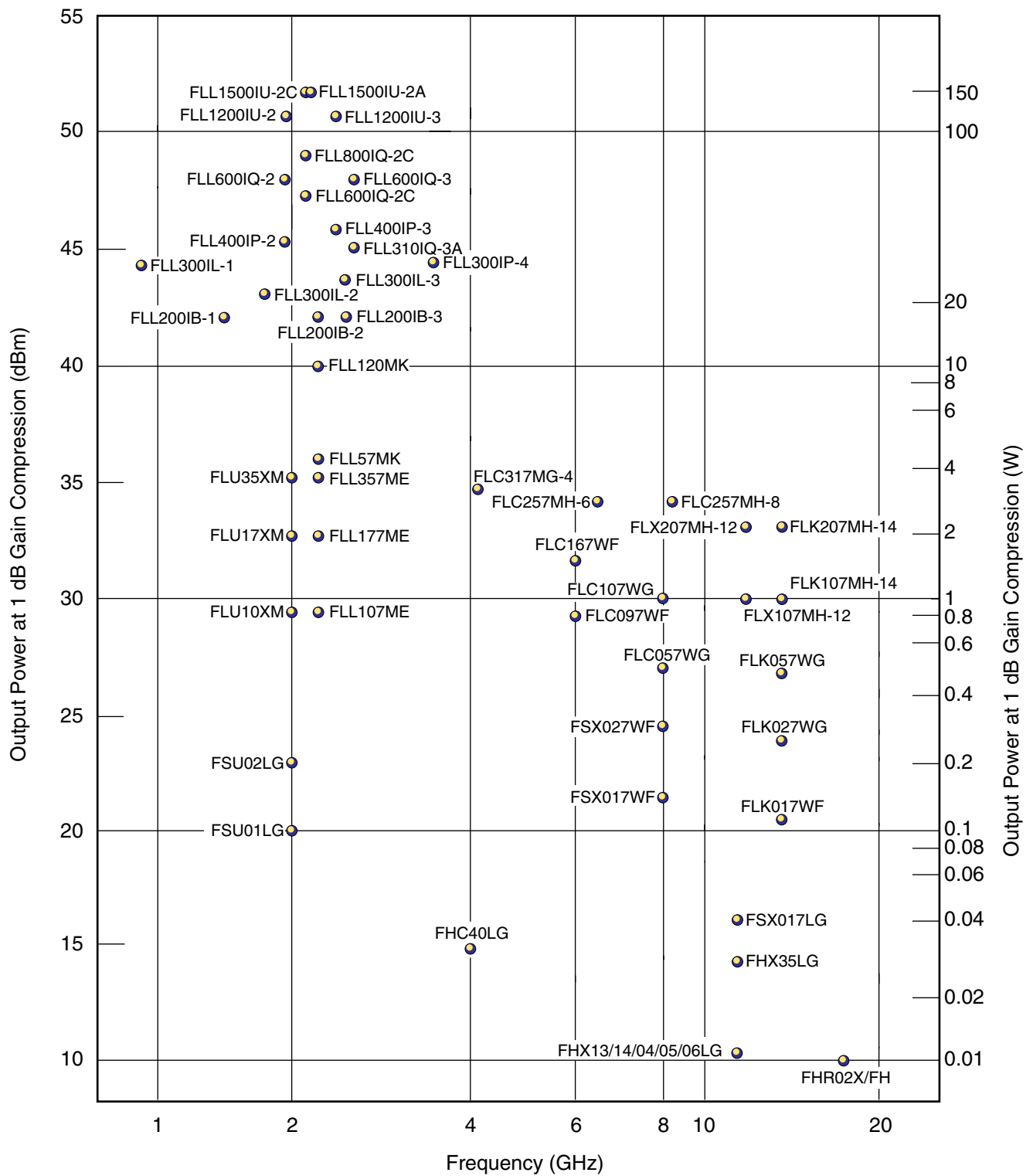
电子元器件系列 (中国.厦门)

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Discrete FETs and HEMTs



エクセリクス製品一覧表 2

ローノイズ・ハイパワーデバイス(High Efficiency Heterojunction Power FETs)

型名	サイズ	CHIP SIZE	W(Gate)/Finger	Bias	P-1dB*	G-1dB*	Freq.	Idss	BVgd**	周波数帯	備考
	um ²	um ²	um		dBm	dB	GHz	mA	V	GHz	
A.) Chips:											
EPA018A	0.3x180	320x290	30	6V, 0.5 Idss	20.0	13.0	18	30-80	15	Up to 65	.75dB NF@12GHz
EPA025A	0.3x250	420x260	62.5	8V, 0.5 Idss	22.5	11.0	18	40-105	15	Up to 45	
EPA030C	0.3x300	330x320	37.5	8V, 0.5 Idss	23.0	11.0	18	50-130	15	Up to 50	
EPA040A	0.3x400	350x340	50	8V, 0.5 Idss	24.5	11.0	18	70-160	15	Up to 45	
EPA060A	0.3x600	500x320	37.5	8V, 0.5 Idss	26.5	10.5	18	105-255	15	Up to 45	
EPA060B/EPA060BV	0.3x600	350x350	60	8V, 0.5 Idss	26.5	10/11.5	18	110-250	15	Up to 40/45	V: Via-hole
EPA080A	0.3x800	510x340	50	8V, 0.5 Idss	27.5	9.5	18	130-320	15	Up to 35	
EPA090A	0.3x900	660x320	37.5	8V, 0.5 Idss	28.0	10.0	18	160-380	15	Up to 40	
EPA120A	0.3x1200	670x340	50	8V, 0.5 Idss	29.5	9.5	18	220-500	15	Up to 30	
EPA120B/EPA120BV	0.3x1200	550x350	60	8V, 0.5 Idss	29.5	9/10.5	18	220-500	15	Up to 30/40	V: Via-hole
EPA120E	0.3x1200	830x320	37.5	8V, 0.5 Idss	29.5	9.5	18	210-510	15	Up to 40	
EPA160A	0.3x1600	840x340	50	8V, 0.5 Idss	31.0	8.5	18	290-660	15	Up to 30	
EPA160B	0.3x1600	540x370	80	8V, 0.5 Idss	31.0	5.5	18	290-660	15	Up to 26	
EPA240B/EPA240BV	0.3x2400	960x350	60	8V, 0.5 Idss	32.5	8/9.5	18	440-940	15	Up to 26/30	V: Via-hole
EPA480B/EPA480BV***	0.4x4800	960x420	120	8V, 0.5 Idss	35.5	7.5/12	12	880-1880	15	Up to 18/30	V: Via-hole
EPA240D	0.4x2400	410x620	240	8V, 0.5 Idss	33.0	20.0	2	440-940	15	Up to 15	
EPA480C	0.4x4800	680x620	240	8V, 0.5 Idss	36.0	19.0	2	880-1880	15	Up to 12	
EPA720A***	0.4x7200	940x620	240	8V, 0.5 Idss	37.5	19.0	2	1320-2820	15	Up to 10	
EPA960B***	0.4x9600	1210x620	240	8V, 0.5 Idss	38.5	18.5	2	1760-3760	15	Up to 10	
EPA1200A***	0.4x12000	1470x620	240	8V, 0.5 Idss	39.5	18.0	2	2200-4700	15	Up to 10	
B.) Non-hermetic Low Cost 70 mils Packages:											
EPA018A-70	0.3x180	-	-	6V, 0.5 Idss	20.0	11.0	18	30-80	15	Up to 30	.75dB NF@12GHz
EPA025A-70	0.3x250	-	-	6V, 0.5 Idss	21.5	8.0	18	40-105	15	Up to 26	
EPA040A-70	0.3x400	-	-	6V, 0.5 Idss	23.5	7.0	18	70-160	15	Up to 26	
EPA060B-70	0.3x600	-	-	6V, 0.5 Idss	25.5	9.0	12	110-250	15	Up to 20	0.4dB,NF;28/31dBm,IP3@2GHz
EPA080A-70	0.3x800	-	-	5V, 0.5 Idss	25.5	7.0	12	130-320	15	Up to 20	

型名	サイズ	CHIP SIZE	W(Gate)/Finger	Bias	P-1dB*	G-1dB*	Freq.	Idss	BVgd**	周波数帯	備考
C.) Hermetic 100 mils Ceramic Flange Packages:											
EPA080A-100F	0.3x800	-	50	8V, 0.5 Idss	27.5	8.5	12	130-320	15	Up to 18	
EPA120B-100F	0.3x1200	-	60	8V, 0.5 Idss	29.5	7.0	12	220-500	15	Up to 18	
EPA160B-100F	0.3x1600	-	80	8V, 0.5 Idss	31.0	5.5	12	290-660	15	Up to 16	
EPA240B-100F	0.3x2400	-	60	8V, 0.5 Idss	32.5	5.5	12	440-940	15	Up to 15	
D.) Surface Mount Plastic Packages:											
EPA018A-SOT23	0.3x180	-	30	6V, 30mA	20.0	17.0	2	30-80	15	Up to 10	0.7dB,NF;27dBm,IP3@2GHz
EPA240D-SOT89	0.4x2400	-	240	8V, 350mA	33.0	14.0	2	440-940	15	Up to 8	0.4dB,NF;38/40dBm,IP3@2GHz
EPA480C-SOT89	0.4x4800	-	240	8V, 750mA	36.0	13.0	2	880-1880	15	Up to 6	0.5dB,NF;41/43dBm,IP3@2GHz

Note: *: Typical Values **: Typical Values measured at Ig=1mA/mm

***: 25um GaAs + 25um PHS(Plated Gold Heat-Sink)